



Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
-20V	$200m\Omega @ V_{GS}= -4.5V$	-2.3A

Description

This new generation of high density MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

Applications

- **DC DC Converters**
- **Power Management Functions**
- **Disconnect Switches**
- Motor Control

Features and Benefits

- Low On-resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)

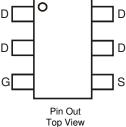
20V P-CHANNEL ENHANCEMENT MODE MOSFET

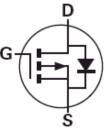
Halogen and Antimony Free."Green" Device (Note 3)

Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.018 grams (Approximate)







Equivalent Circuit

Ordering Information (Note 4)

Part Number	Reel Size (inch)	Tape Width (mm)	Quantity Per Reel
ZXM62P02E6TA	7	8	3,000
ZXM62P02E6TC	13	8	10,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. Notes:

2. See http://www.diodes.com/quality/lead free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimining compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Π	Π	П
	2P02	Σž
0		
		\Box

2P02 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: C = 2015) M or \overline{M} = Month (ex: 9 = September)

Date Code K	ey											
Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026
Code	С	D	E	F	G	Н	I	J	K	L	М	N
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	Р



Absolute Maximum Ratings

(Characteristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±12	V
		T _A = +25°C (Note 6)	I	-2.3	•
Continuous Drain Current	$V_{GS} = -4.5V$	T _A = +70°C (Note 6)	ID	-1.7	A
Pulsed Drain Current		(Note 7)	I _{DM}	-13	A
Continuous Source Current (Body Diode)		(Note 6)	ls	-1.9	A
Pulsed Source Current (Body Diode)		(Note 7)	I _{SM}	-13	A
Power Dissipation at T _A = +25°C Linear Derating Factor		(Note 5)	PD	1.1 8.8	W mW/°C
Power Dissipation at $T_A = +25^{\circ}C$ Linear Derating Factor		(Note 6)	PD	1.7 13.7	W mW/°C
Operating and Storage Temperature Range			TJ, T _{STG}	-55 to +150	°C

Thermal Resistance

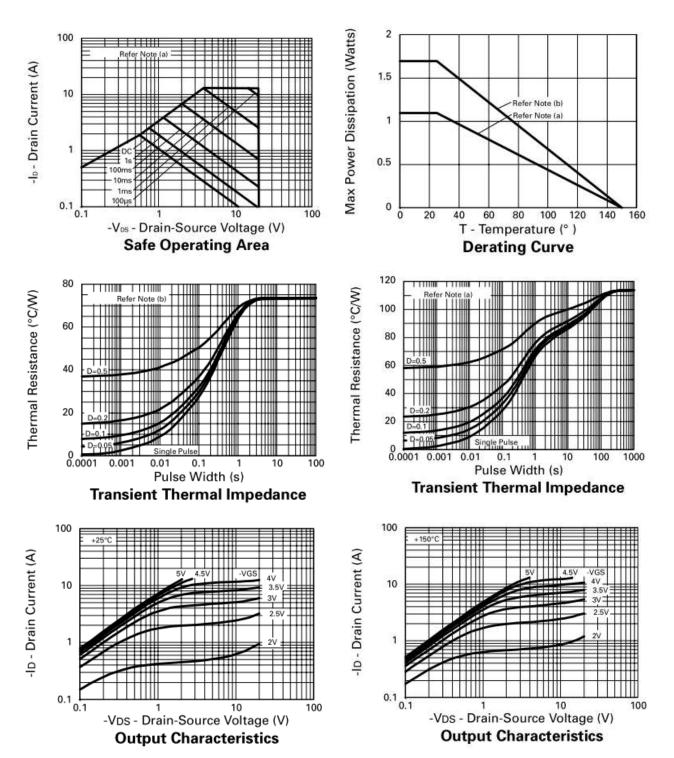
Characteristic	Symbol	Value	Unit	
lunction to Ambient	(Note 5)	C	113	0 0 AN
Junction to Ambient	(Note 6)	R _{θJA}	73	°C/W

Electrical Characteristics (@T_A = +25°C, unless otherwise stated.)

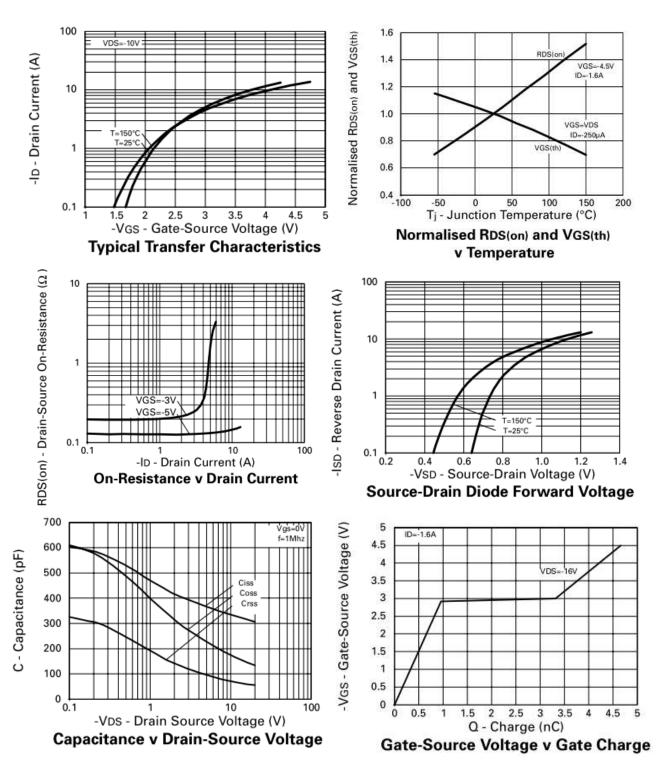
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
STATIC							
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μA	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
Gate Threshold Voltage	V _{GS(TH)}	-0.7	_	_	V	$I_D = -250 \mu A$, $V_{DS} = V_{GS}$	
Otatia Dusia Osuma Os Dusistana (Nata O)	5			0.2	Ω	$V_{GS} = -4.5V, I_D = -1.6A$	
Static Drain-Source On-Resistance (Note 8)	R _{DS(ON)}	_		0.375	Ω	$V_{GS} = -2.7V, I_D = -0.8A$	
Forward Transconductance (Note 10)	g fs	1.5	_	_	S	$V_{DS} = -10V, I_{D} = -0.8A$	
DYNAMIC (Note 10)			•	•	•	•	
Input Capacitance	C _{iss}	_	320	_	pF		
Output Capacitance	Coss	_	150	_	pF	$ \nabla_{\text{VS}} = -15\text{V}, \ \text{V}_{\text{GS}} = 0\text{V} $ - f = 1MHz	
Reverse Transfer Capacitance	Crss		75	_	pF		
SWITCHING (Notes 9 and10)	·				•		
Total Gate Charge	Qg		_	5.8	nC	V _{DS} = -16V, V _{GS} = -4.5V	
Gate-Source Charge	Q _{gs}	_	—	1.25	nC	$I_{\rm D} = -1.6{\rm A}$	
Gate-Drain Charge	Q _{gd}		_	2.8	nC	(Refer to test circuit)	
Turn-On Delay Time	t _{D(ON)}		4.1	_	ns		
Turn-On Rise Time	t _R		15.4	_	ns	$V_{DD} = -10V, I_D = -1.6A, R_G = 6\Omega,$	
Turn-Off Delay Time	t _{D(OFF)}	_	12.0	_	ns	$R_D = 6.1\Omega$ (Refer to test circuit)	
Turn-Off Fall Time	tF		19.2	_	ns		
SOURCE-DRAIN DIODE			•	•	•	•	
Diode Forward Voltage (Note 8)	V _{SD}	_		-0.95	V	T _J = +25°C, I _S =-1.6A, V _{GS} =0V	
Reverse recovery time (Note 10)	t _{RR}	_	22.5	—	ns	T _J = +25°C, I _F =-1.6A,	
Reverse recovery charge (Note 10)	Q _{RR}	_	10.4		nC	di/dt= 100A/µs	

 5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.
6. For a device surface mounted on FR-4 PCB measured at t ≤ 5 secs.
7. Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.
8. Measured under pulsed conditions. Width= 300µs; duty cycle ≤ 2%.
9. Switching characteristics are independent of operating junction temperatures.
10. For design aid only, not subject to production testing. Notes:



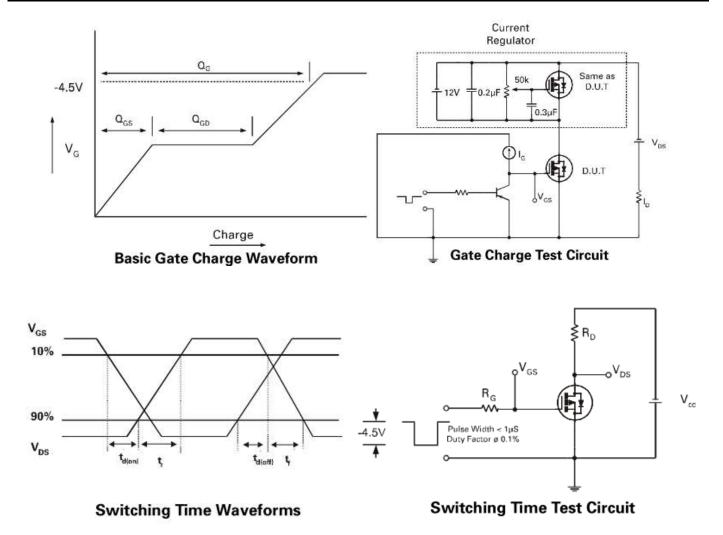








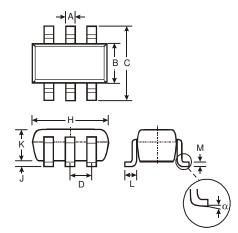
Test Circuits





Package Outline Dimensions

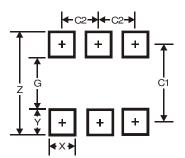
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



Dim A B	Min 0.35 1.50 2.70	Max 0.50 1.70 3.00	Typ 0.38 1.60			
В	1.50	1.70	1.60			
-						
	2.70	3 00	000			
С		5.00	2.80			
D			0.95			
Η	2.90	3.10	3.00			
J	0.013	0.10	0.05			
Κ	1.00	1.30	1.10			
L	0.35	0.55	0.40			
М	0.10	0.20	0.15			
α	α 0° 8° —					
All D	imensi	ons in	mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95



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